

# Magnetic and structural properties of manganese doped (Al,Ga)N studied with Emission Mössbauer Spectroscopy

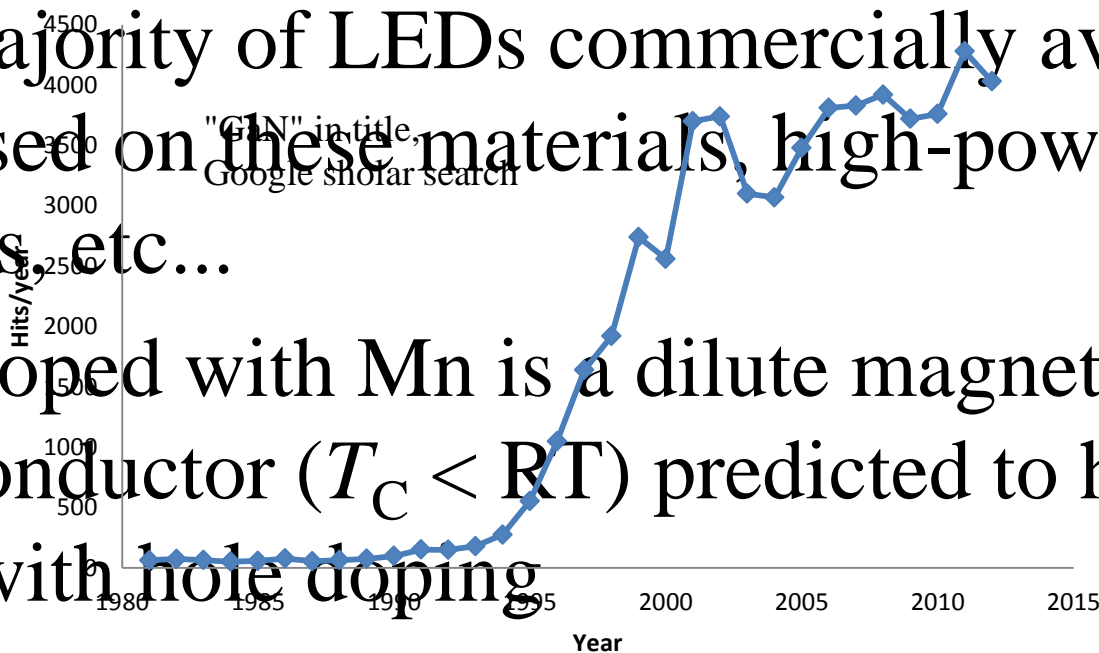


Proposal to the ISOLDE and  
Neutron Time-of-Flight Committee

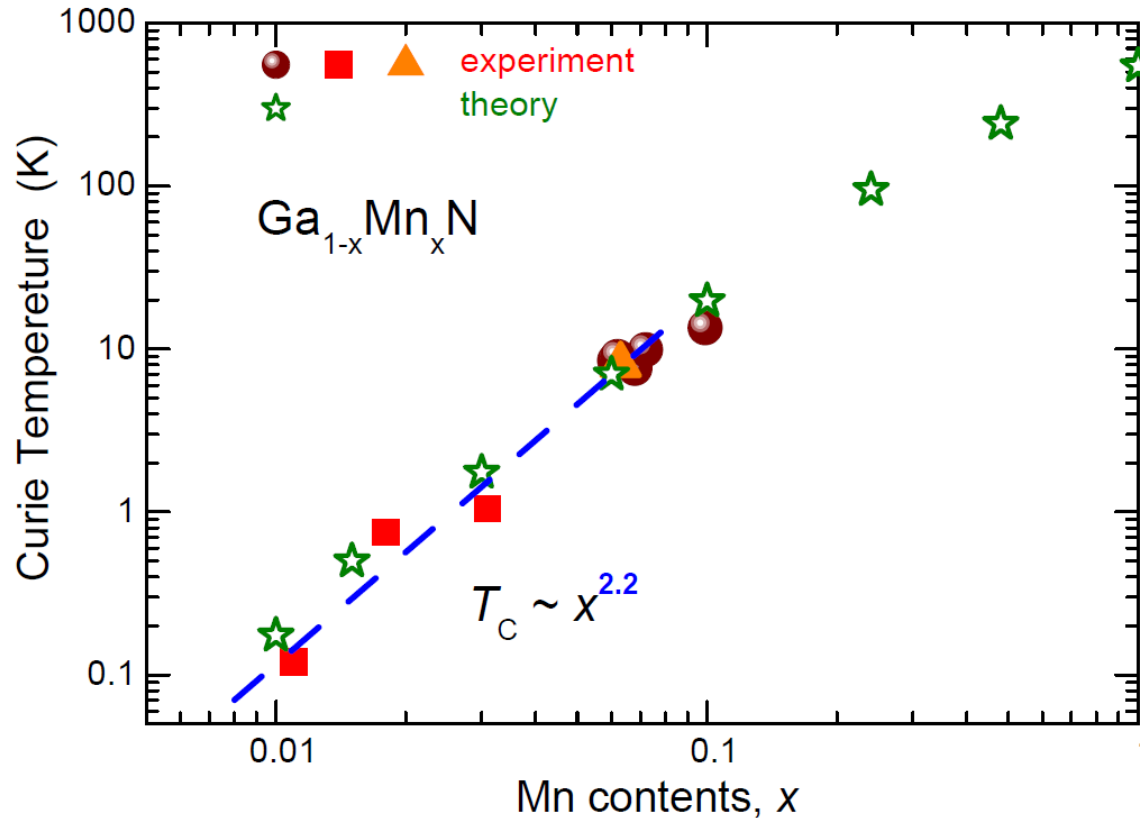
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- Contact person: Karl Johnston

# Why study Nitride III-V's

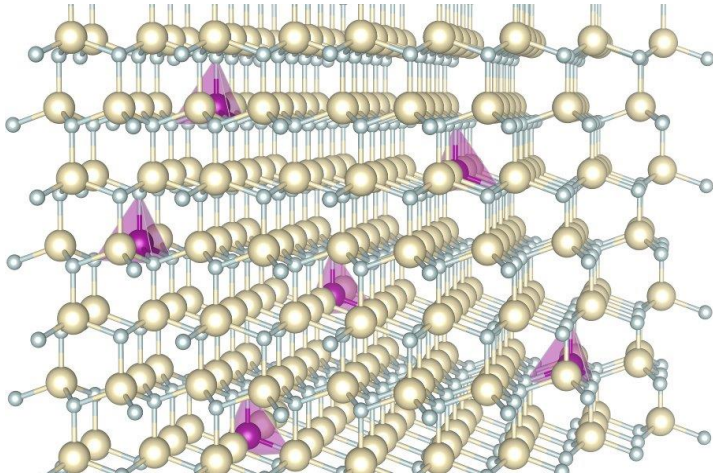
- Importance of (GaN, AlN, InN) system
- The majority of LEDs commercially available are based on these materials, high-power devices, etc...
- GaN doped with Mn is a dilute magnetic semiconductor ( $T_C < RT$ ) predicted to have  $T_C > RT$  with hole doping



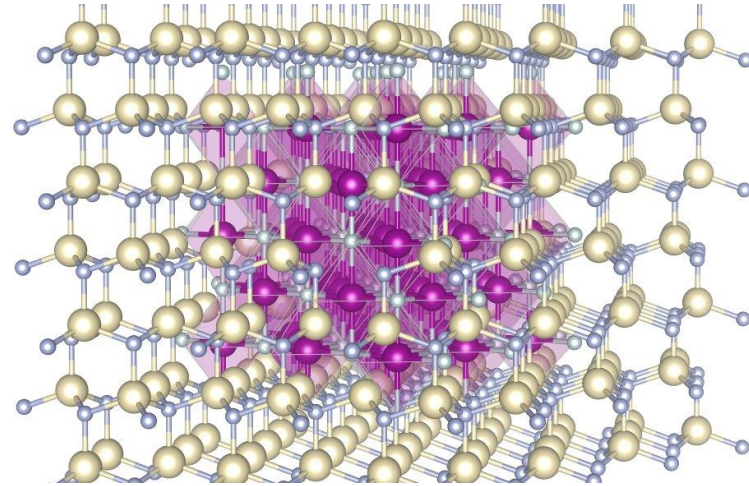
# Dilute magnetism in GaN



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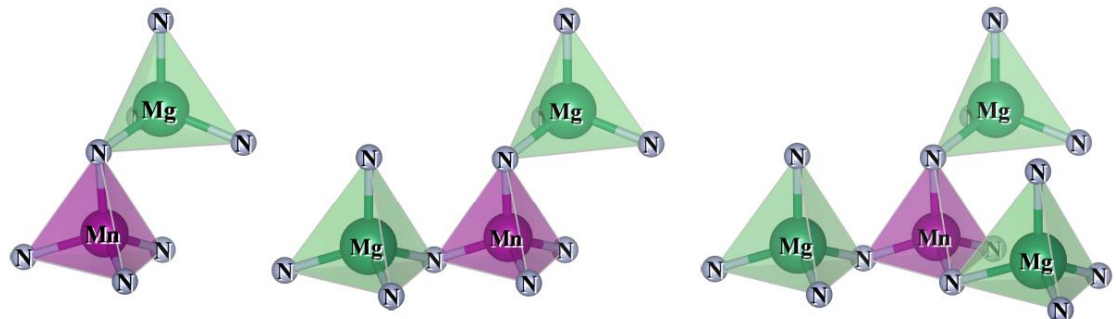
dilute magnetic semiconductors  
(superexchange interaction provided)



condensed magnetic semiconductors  
(we can produce ordered arrays of magnetic nanocrystals)

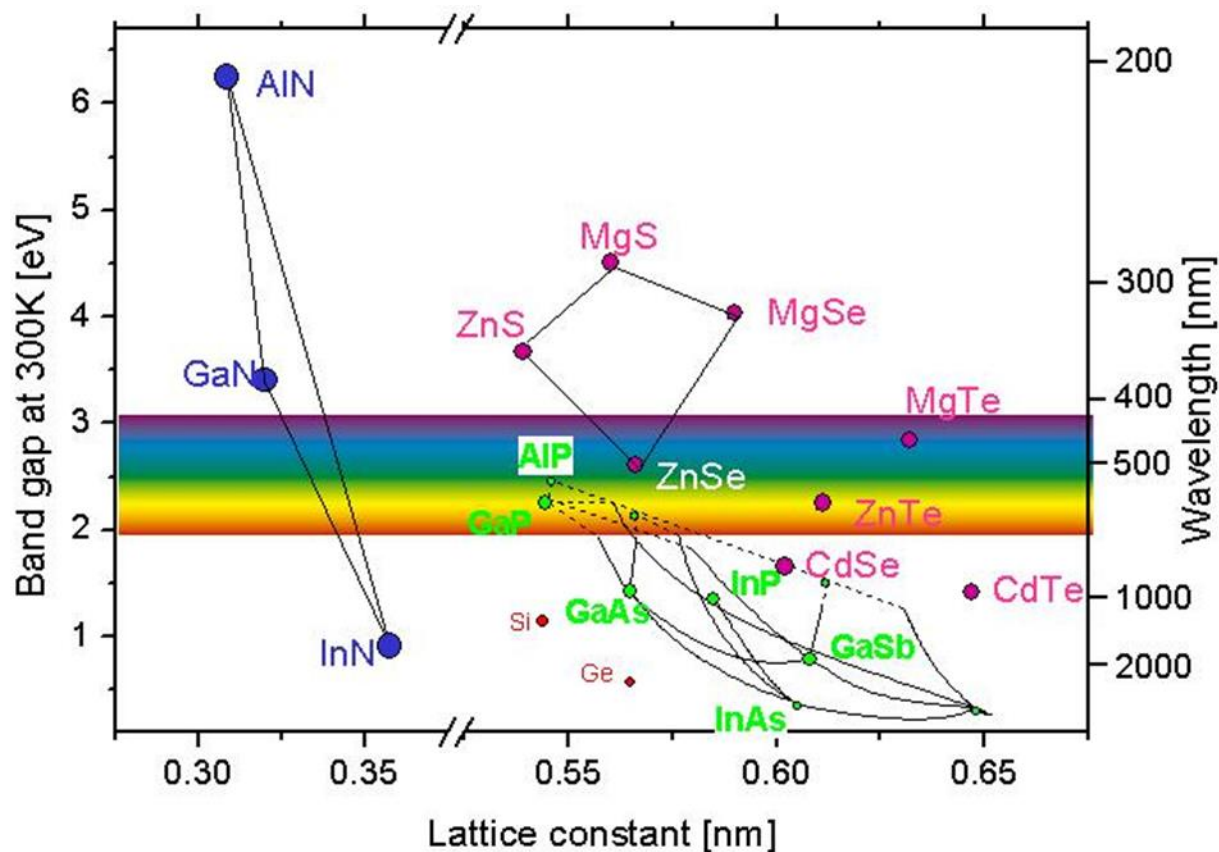
+ Mg/structural defects:

functional Mn/Mg complexes which allow tuning of the spin state and the optical properties of the system



# Why study (Al,Ga)N ?

- One can tune the band gap over an exceptionally large range



GaN  $\rightarrow$  AlGaN  
 ( $a_0$  engineering):

$\Rightarrow$  Tuning of band-gap & magnetism (p-d hybridization)

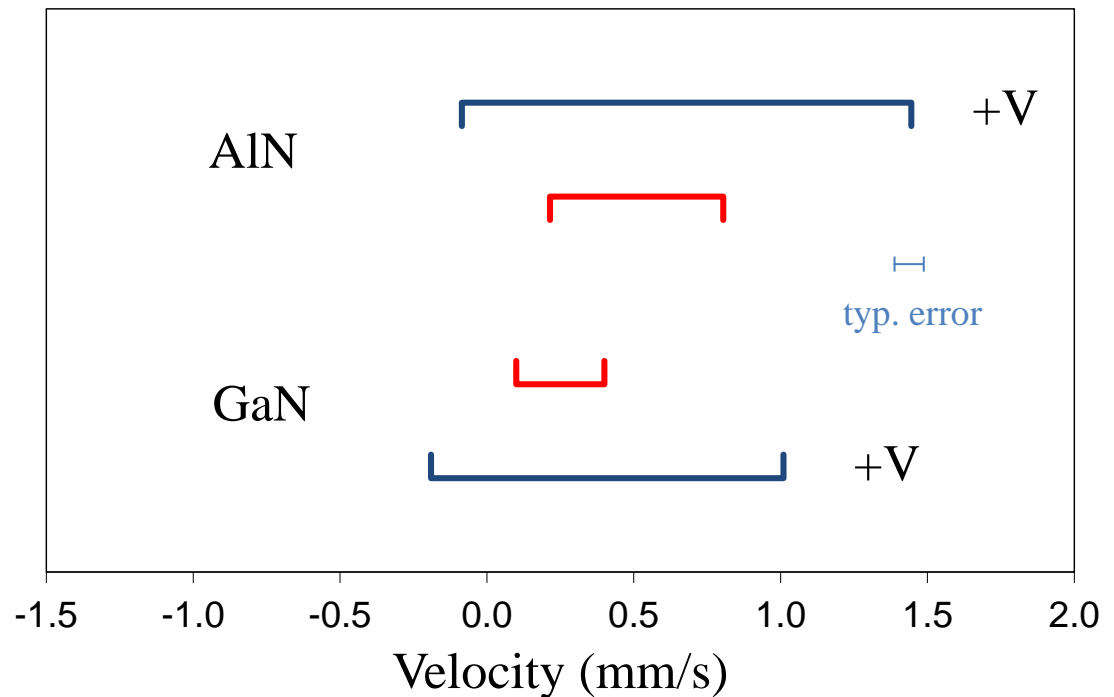
[Navarro APL 101 (2012) 081911]

# Why ISOLDE?

- We can apply  $^{57}\text{Mn}$  ( $T_{1/2}=1.5$  min.)  $\rightarrow$   $^{57}\text{MFe}$
- Use *emission* Mössbauer spectroscopy
  - Valence(/spin) state of probe atom ( $\text{Fe}^{n+}$ ,  $\text{Sn}^{n+}$ )
  - Symmetry of lattice site ( $V_{zz}$ )
    - Differ amorphous/point-defects (angular dependence)
  - *Diffusion of probe atoms (few jumps  $\sim 100$  ns)*
  - *Binding properties (Debye-Waller factors)*
  - Magnetic interactions (ferro/para)
  - Paramagnetic relaxation ( $\sim 10^7$ - $10^8$  Hz)
- Can usually detect and distinguish up to 4-5 spectral components (substitutional, interstitial, damage, vacancy-defects,...)

# Feasibility of current proposal:

- Already have data on end-members
- **Substitutional Fe ( $\text{Fe}_S$ )**
- Fe-V complexes ( $\text{Fe}_C$ )
- $\text{Fe}^{3+}$



# Feasibility: Material

- (Al,Ga)N:Mn made by MOVPE (metalorganic vapour phase epitaxy)
- Characterization:
  - HRTEM, EELS;
  - HRXRD and synchrotron XRD;
  - synchrotron XANES and EXAFS;
  - magneto-photoluminescence;
  - SQUID magnetometry;
  - EPR (electron paramagnetic resonance);
  - magneto-transport.



# Experimental plan:

- Temperature series:  $^{57}\text{Mn}$ , 2-4 h per series
  - Site populations
  - Annealing of defect
  - Spin lattice relaxation rates
  - ~5 (Al,Ga)N compositions
  - 3.5% Mn doped ~5 (Al,Ga)N compositions
  - Specific (Al,Ga)N and ~5 Mn concentrations
- External B field, angular measurements, isothermal annealing, quenching experiments (HT impl/LT meas) + ...
- $^{119}\text{In}$  (2.3 min)  $\rightarrow$   $^{119\text{M}}\text{Sn}$ ;  $^{57}\text{Co}$  (272 d)  $\rightarrow$   $^{57\text{M}}\text{Fe}$  measurements

# Formal beam request:

Isotope ( $T_{1/2}$ )	Minimum Intensity ( $\mu\text{Ci}$ )	Energy (keV)	Shifts	Target	Ion source
$^{57}\text{Mn}$ (1.5 min)	$(2-3) \times 10^8$	$\geq 50$	9	$\text{UC}_x$	Mn RILIS
$^{119}\text{In}$ (2.3 min)	$(2-3) \times 10^8$	$\geq 50$	2	$\text{UC}_x$	In RILIS
$^{57}\text{Co}$ (270 d)	$9 \times 10^7$	$\geq 50$	2	$\text{ZrO}_2$ or $\text{YtO}_2$	VADIS or Co RILIS
<b>Total</b>			<b>13</b>		

# Mössbauer collaboration at ISOLDE/CERN



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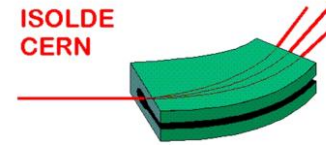
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# Funding agencies involved

## European Research Council [ERC] funded project

[ERC1] ERC Advanced Grant [P 227690]  
FunDMS - Functionalisation of diluted magnetic semiconductors

## European Commission funded network

[Net1] EC FP7 Marie Curie Networks - Marie Curie Initial Training Network on Nanoscale Semiconductor Spintronics SemiSpinNet [EU FP7 215368];

## European Commission funded action

[EC1] REGPOT-2012-2013-1, FP7 CAPACITIES  
“European Action towards a Leading Centre for Innovative Materials”  
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## FWF – Austrian Science Fund

### [Fonds zur Förderung der wissenschaftlichen Forschung] funded projects

[FWF1] “Magnetic nitrides probed via microwave resonances” [P24471]  
[FWF2] “Determination of ferromagnetic phase diagram in nitrides” [P22477]  
[FWF3] “Controlling the formation of magnetic nanocrystals in diluted magnetic Semiconductors” [P20065]  
[FWF4] “Carrier-induced ferromagnetism in (Ga,Fe)N” [P17169]

## Danish National Science Foundation

Travel grants for CERN related research

## Icelandic Centre for Research (RANNIS)

## National Research Foundation/Department of Science and Technology, South Africa

